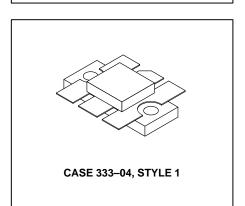
# The RF Line NPN Silicon RF Power Transistor

Designed primarily for wideband large—signal output and driver amplifier stages in the 400 to 512 MHz frequency range.

- Specified 28 Volt, 470 MHz Characteristics
   Output Power = 80 Watts
   Minimum Gain = 7.3 dB
   Efficiency = 50% (Min)
- Built-In Matching Network for Broadband Operation
- 100% Tested for Load Mismatch at all Phase Angles with 30:1 VSWR
- · Gold Metallization System for High Reliability Applications

# **MRF338**

80 W, 400 to 512 MHz CONTROLLED "Q" BROADBAND RF POWER TRANSISTOR NPN SILICON



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#### **MAXIMUM RATINGS**

Rating	DataSheet4U.com	Symbol	Value	Unit
Collector–Emitter Voltage		VCEO	30	Vdc
Collector-Base Voltage		VCBO	60	Vdc
Emitter–Base Voltage		VEBO	4	Vdc
Collector Current — Continuous — Peak		lC	9 12	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C (1) Derate above 25°C		PD	250 1.43	Watts W/°C
Storage Temperature Range		T <sub>stg</sub>	-65 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic		Max	Unit
Thermal Resistance, Junction to Case (2)		0.7	°C/W

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (IC = 80 mAdc, IB = 0)	V(BR)CEO	30	_	_	Vdc
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 80 mAdc, V <sub>BE</sub> = 0)	V(BR)CES	60	_	_	Vdc
(IE = 8 mAdc, IC = 0)	V(BR)EBO	4	_	_	Vdc

- (1) This device is designed for RF operation. The total device dissipation rating applies only when the device is operated as an RF amplifier.
- (2) Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.

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# **ELECTRICAL CHARACTERISTICS** — **continued** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Base Breakdown Voltage (IC = 80 mAdc, IE = 0)	V(BR)CBO	60	_	_	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 30 Vdc, I <sub>E</sub> = 0)	ICBO	_	_	5	mAdc
ON CHARACTERISTICS			•		
DC Current Gain (I <sub>C</sub> = 4 Adc, V <sub>CE</sub> = 5 Vdc)	hFE	20	_	80	_
DYNAMIC CHARACTERISTICS			•		
Output Capacitance (V <sub>CB</sub> = 28 Vdc, I <sub>E</sub> = 0, f = 1 MHz)	C <sub>ob</sub>	_	95	125	pF
FUNCTIONAL TESTS (Figure 1)			•		
Common–Emitter Amplifier Power Gain (V <sub>CC</sub> = 28 Vdc, P <sub>Out</sub> = 80 W, f = 470 MHz)	G <sub>PE</sub>	7.3	8.8	_	dB
Collector Efficiency (V <sub>CC</sub> = 28 Vdc, P <sub>out</sub> = 80 W, f = 470 MHz)	η	50	60	_	%
Load Mismatch (V <sub>CC</sub> = 28 Vdc, P <sub>out</sub> = 80 W, f = 470 MHz, VSWR = 30:1, All Phase Angles at Frequency of Test)	Ψ	N	o Degradation	in Output Pov	ver

RFC1 C12 C15 R2 C11 L2 R1 Z2 OUTPUT DUT INPUT C6 **+** C7 C2 = = C3 = BEAD C5

Ferroxcube #56-590-65/3B 3 Turns #18 AWG, 0.185" ID, Close Wound Bead L3 C1, C2, C8, C9 0.8-20 pF, Johanson (JMC 5501) L4 4 Turns #18 AWG, 0.185" ID, Close Wound C3, C4, C6, C7 25 pF, 100 V, Underwood RFC1 Ferroxcube VK200 19/4B C5, C10 100 pF, 100 V, Underwood R1, R2 10 Ω, 2.0 Watt Carbon C11, C13 0.1 μF, Erie Redcap Z1 0.190" W x 2.5" L, Microstrip Lin 680 pF, Feedthru C12, C14 Z2 0.190" W x 0.289" L, Microstrip Line 1.0 μF, Tantalum Z3 C15 0.190" W x 0.55" L, Microstrip Line L1 0.15 µH, Molded Choke Ζ4 0.190" W x 0.325" L, Microstrip Line L2 5 Turns #20 AWG, 0.185" ID, Close Wound Board Glass Teflon, t = 0.062'',  $\epsilon_{\Gamma} = 2.56$ 

Figure 1. 470 MHz Test Circuit

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## **TYPICAL CHARACTERISTICS**

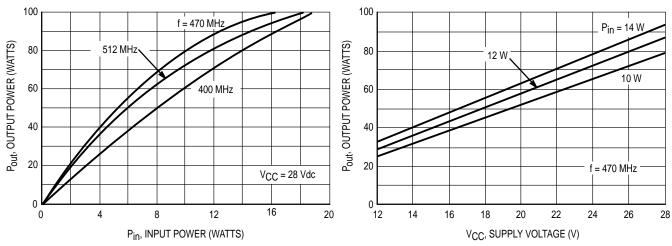


Figure 2. Output Power versus Input Power

Figure 3. Output Power versus Supply Voltage

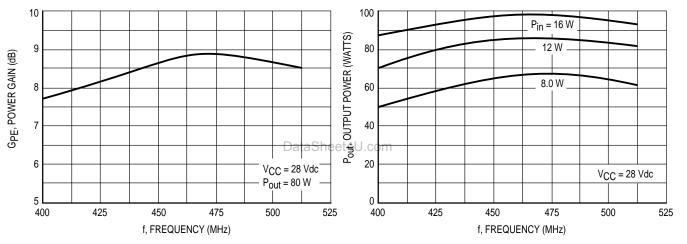


Figure 4. Power Gain versus Frequency

Figure 5. Output Power versus Frequency

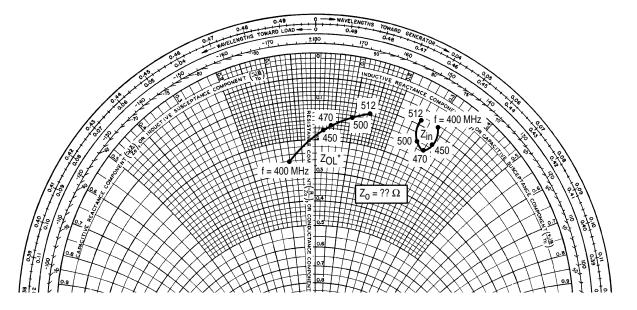
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MOTOROLA RF DEVICE DATA

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V <sub>CC</sub> = 28 V, P <sub>out</sub> = 80 W				
f	Z <sub>in</sub>	Z <sub>OL</sub> *		
MHz	Ohms	Ohms		
512	0.91 + j2.61	1.19 + j1.34		
500	1.47 + j2.71	1.33 + j0.96		
470	1.53 + j2.98	1.60 + j0.45		
450	1.27 + j3.09	1.70 + j0.25		
400	0.86 + j3.01	2.58 – j0.79		

 $Z_{OL}^{\star}$  = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

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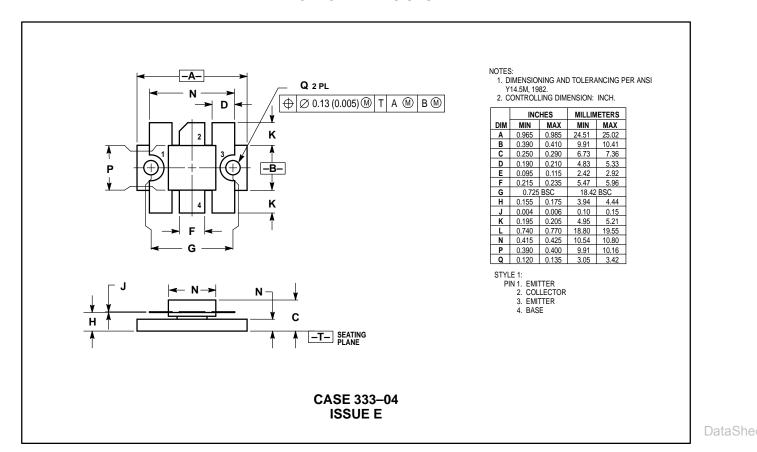
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Figure 6. Series Equivalent Input/Output Impedance

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MRF338 MOTOROLA RF DEVICE DATA

## **PACKAGE DIMENSIONS**



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